

N-Channel 12-V (D-S) MOSFET

CHARACTERISTICS

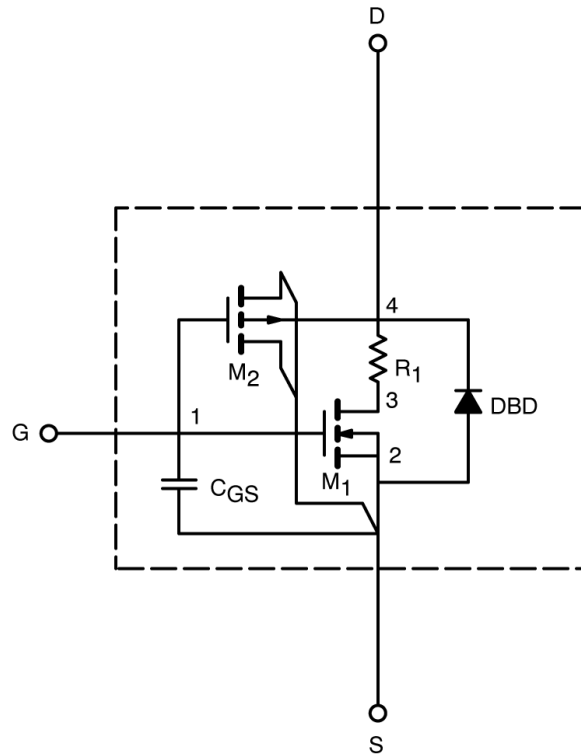
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0-to-5V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



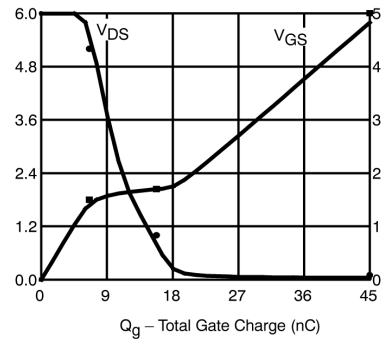
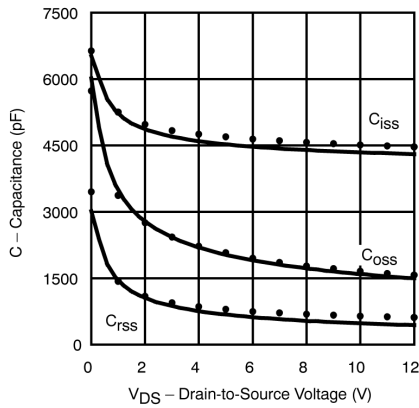
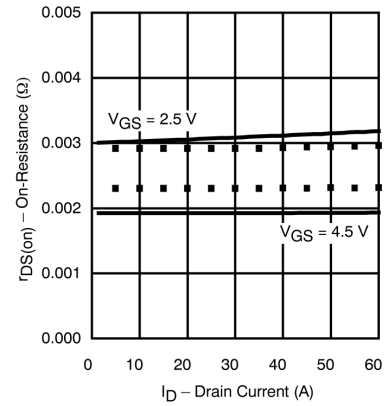
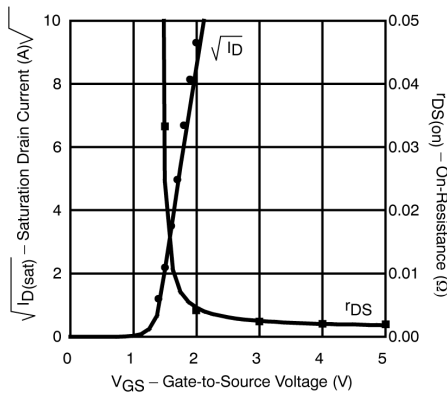
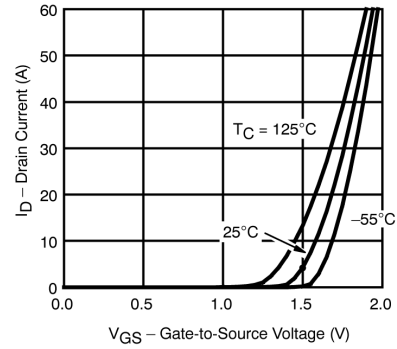
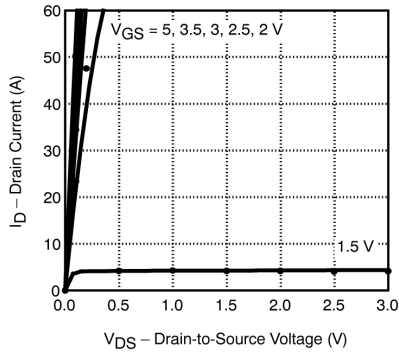
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Conditions	Simulated Data	Measured Data	Unit
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.91		V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{V}, V_{GS} = 4.5\text{V}$	1265		A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 25\text{A}$	0.0019	0.0024	Ω
		$V_{GS} = 2.5\text{V}, I_D = 20\text{A}$	0.0031	0.0031	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 6\text{V}, I_D = 25\text{A}$	142	130	S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\text{A}, V_{GS} = 0\text{V}$	0.76	0.75	V
Dynamic^b					
Total Gate Charge	Q_g	$V_{DS} = 6\text{V}, V_{GS} = 4.5\text{V}, I_D = 25\text{A}$	42	40	nC
Gate-Source Charge	Q_{gs}		6.7	6.7	
Gate-Drain Charge	Q_{gd}		9.2	9.2	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\text{V}, R_L = 6\Omega$ $I_D \cong 1\text{A}, V_{GEN} = 4.5\text{V}, R_G = 6\Omega$	41	40	ns
Rise Time	t_r		58	40	
Turn-Off Delay Time	$t_{d(off)}$		66	140	
Fall Time	t_f		118	70	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\text{A}, di/dt = 100\text{ A}/\mu\text{s}$	39	50	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J=25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.